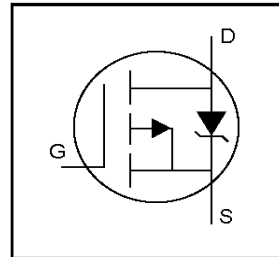


IRFR5505PbF
IRFU5505PbF

- Ultra Low On-Resistance
- P-Channel
- Surface Mount (IRFR5505)
- Straight Lead (IRFU5505)
- Advanced Process Technology
- Fast Switching
- Fully Avalanche Rated
- Lead-Free
- Halogen-Free

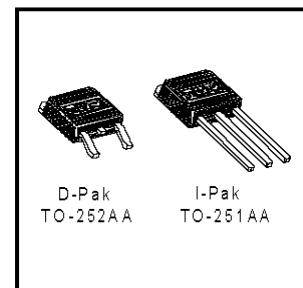


$V_{DSS} = -55V$
$R_{DS(on)} = 0.11\Omega$
$I_D = -18A$

Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The D-Pak is designed for surface mounting using vapor phase, infrared, or wave soldering techniques. The straight lead version (IRFU series) is for through-hole mounting applications. Power dissipation levels up to 1.5 watts are possible in typical surface mount applications.



Absolute Maximum Ratings

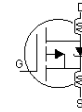
	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	-18	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	-11	
I_{DM}	Pulsed Drain Current ①	-64	
$P_D @ T_C = 25^\circ C$	Power Dissipation	57	W
	Linear Derating Factor	0.45	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy②	150	mJ
I_{AR}	Avalanche Current①	-9.6	A
E_{AR}	Repetitive Avalanche Energy①	5.7	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-5.0	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	---	2.2	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mount)**	---	50	
$R_{\theta JA}$	Junction-to-Ambient	---	110	

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	-55	---	---	V	V _{GS} = 0V, I _D = -250μA
ΔV _{(BR)DSS/ΔT_J}	Breakdown Voltage Temp. Coefficient	---	-0.049	---	V/°C	Reference to 25°C, I _D = -1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	---	---	0.11	Ω	V _{GS} = -10V, I _D = -9.6A ③
V _{GS(th)}	Gate Threshold Voltage	-2.0	---	-4.0	V	V _{DS} = V _{GS} , I _D = -250μA
g _{fs}	Forward Transconductance	4.2	---	---	S	V _{DS} = -25V, I _D = -9.6A
I _{DSS}	Drain-to-Source Leakage Current	---	---	-25	μA	V _{DS} = -55V, V _{GS} = 0V
		---	---	-250	μA	V _{DS} = -44V, V _{GS} = 0V, T _J = 150°C
I _{GSS}	Gate-to-Source Forward Leakage	---	---	-100	nA	V _{GS} = 20V
	Gate-to-Source Reverse Leakage	---	---	100	nA	V _{GS} = -20V
Q _g	Total Gate Charge	---	---	32	nC	I _D = -9.6A
Q _{gs}	Gate-to-Source Charge	---	---	7.1	nC	V _{DS} = -44V
Q _{gd}	Gate-to-Drain ("Miller") Charge	---	---	15	nC	V _{GS} = -10V, See Fig. 6 and 13 ④
t _{d(on)}	Turn-On Delay Time	---	12	---	ns	V _{DD} = -28V I _D = -9.6A R _G = 2.6Ω R _D = 2.8Ω, See Fig. 10 ④
t _r	Rise Time	---	28	---		
t _{d(off)}	Turn-Off Delay Time	---	20	---		
t _f	Fall Time	---	16	---		
L _D	Internal Drain Inductance	---	4.5	---	nH	Between lead, 6mm (0.25in.) from package and center of die contact ⑤
L _S	Internal Source Inductance	---	7.5	---		
C _{ISS}	Input Capacitance	---	650	---	pF	V _{GS} = 0V V _{DS} = -25V f = 1.0MHz, See Fig. 5
C _{OSS}	Output Capacitance	---	270	---		
C _{RSS}	Reverse Transfer Capacitance	---	120	---		



Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	---	---	-18	A	MOSFET symbol showing the integral reverse p-n junction diode.
I _{SM}	Pulsed Source Current (Body Diode) ①	---	---	-64		
V _{SD}	Diode Forward Voltage	---	---	-1.6	V	T _J = 25°C, I _S = -9.6A, V _{GS} = 0V ④
t _{rr}	Reverse Recovery Time	---	51	77	ns	T _J = 25°C, I _F = -9.6A
Q _{rr}	Reverse Recovery Charge	---	110	160	nC	di/dt = 100A/μs ④
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

② Starting T_J = 25°C, L = 3.2mH
R_G = 25Ω, I_{AS} = -9.6A. (See Figure 12)

③ I_{SD} ≤ -9.6A, di/dt ≤ 290A/μs, V_{DD} ≤ V_{(BR)DSS},
T_J ≤ 150°C

④ Pulse width ≤ 300μs; duty cycle ≤ 2%.

⑤ This is applied for I-PAK, L_S of D-PAK is measured between lead and center of die contact

** When mounted on 1" square PCB (FR-4 or G-10 Material) .

For recommended footprint and soldering techniques refer to application note #AN-994

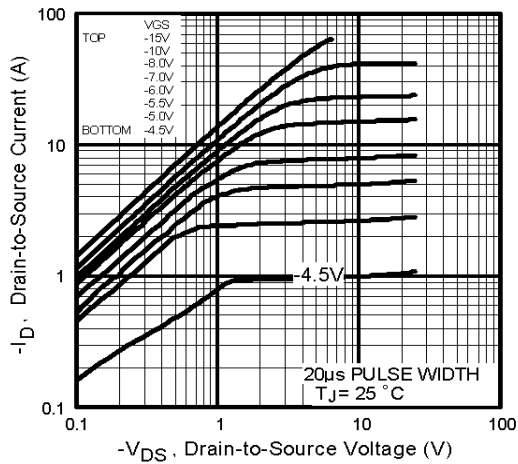


Fig 1. Typical Output Characteristics

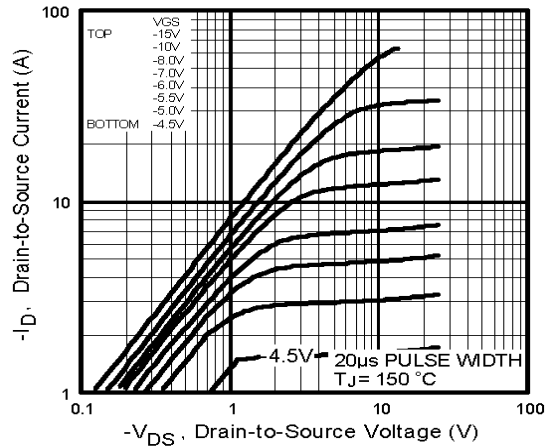


Fig 2. Typical Output Characteristics

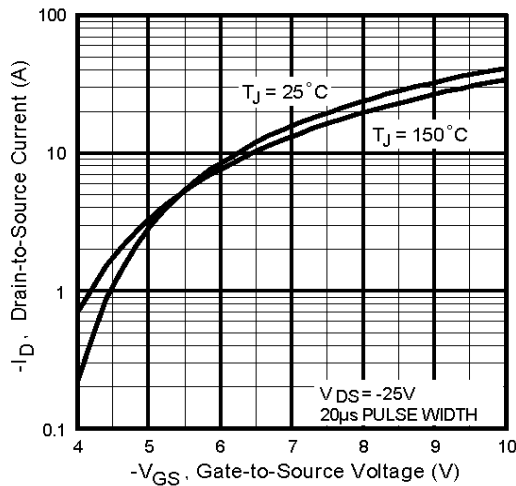


Fig 3. Typical Transfer Characteristics

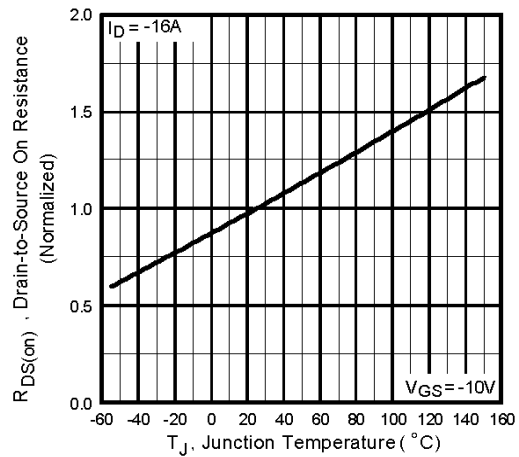


Fig 4. Normalized On-Resistance Vs. Temperature

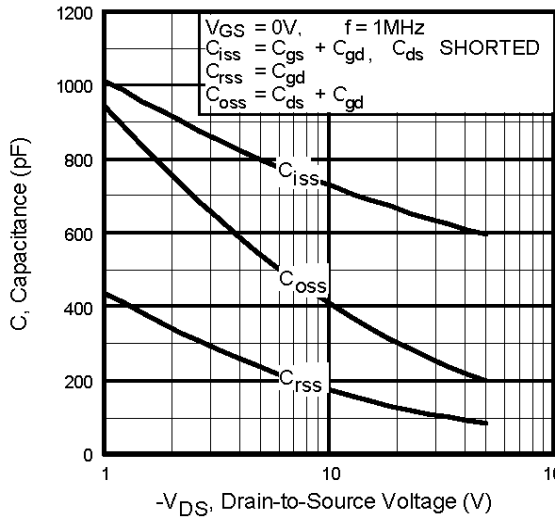


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

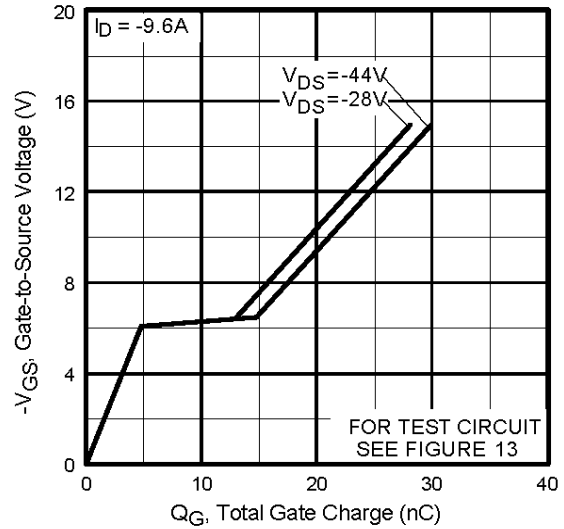


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

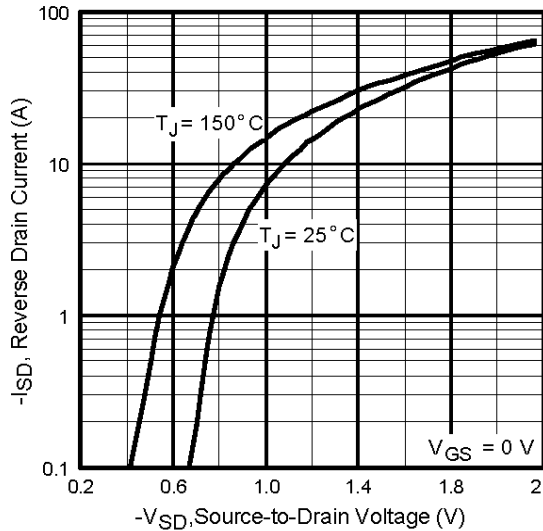


Fig 7. Typical Source-Drain Diode Forward Voltage

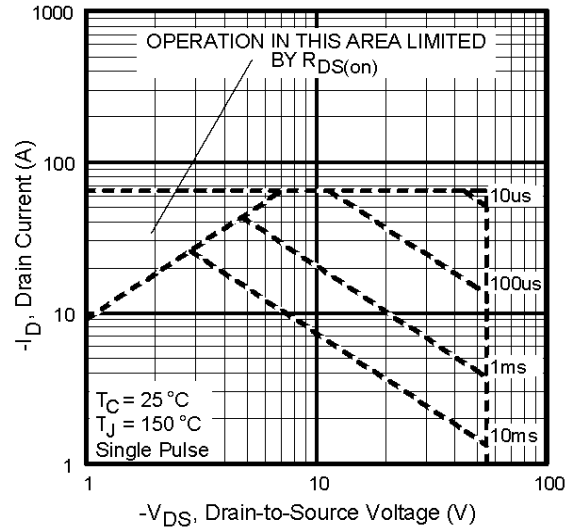


Fig 8. Maximum Safe Operating Area

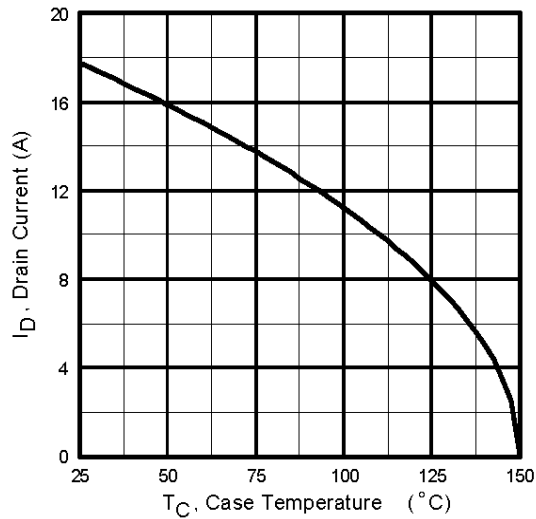


Fig 9. Maximum Drain Current Vs. Case Temperature

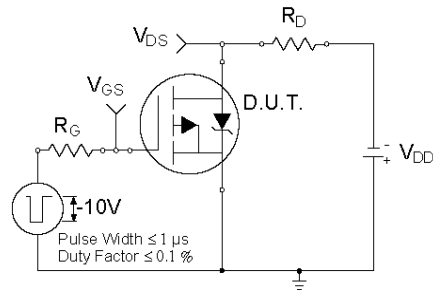


Fig 10a. Switching Time Test Circuit

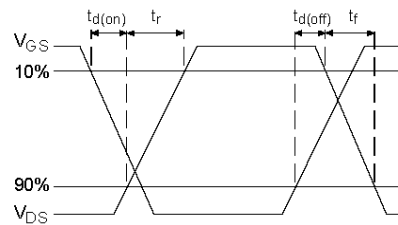


Fig 10b. Switching Time Waveforms

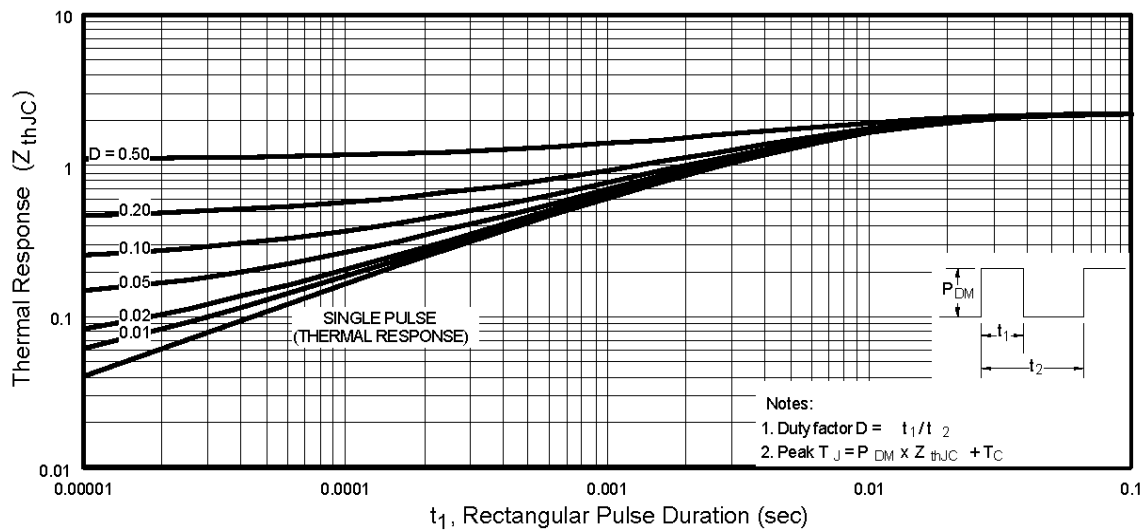


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

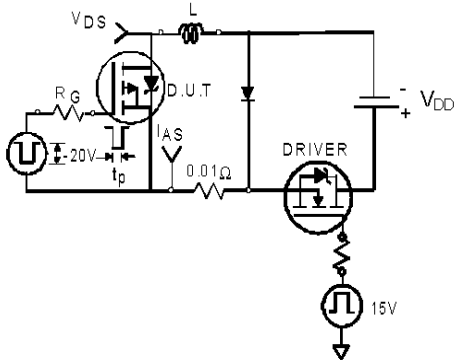


Fig 12a. Unclamped Inductive Test Circuit

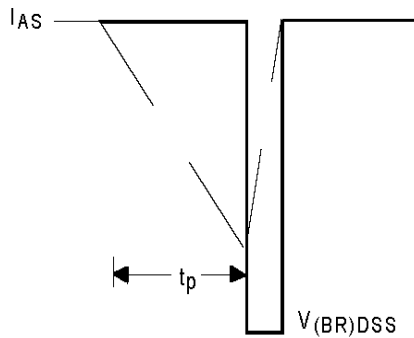


Fig 12b. Unclamped Inductive Waveforms

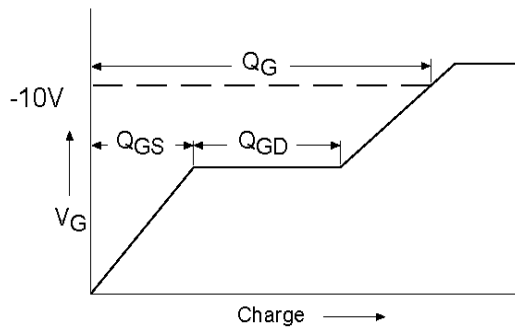


Fig 13a. Basic Gate Charge Waveform

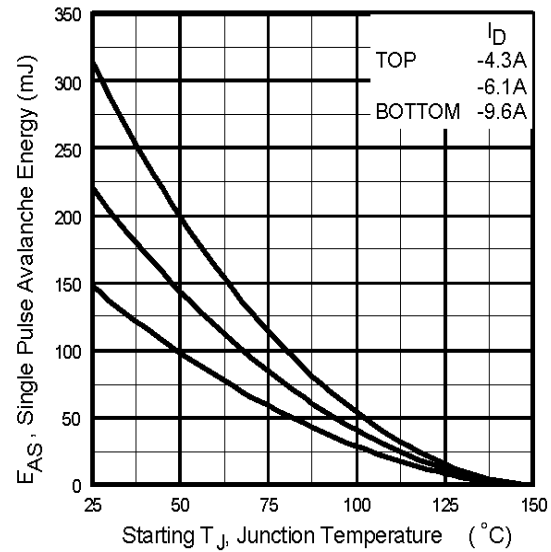


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

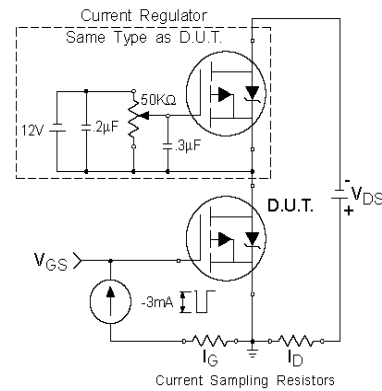
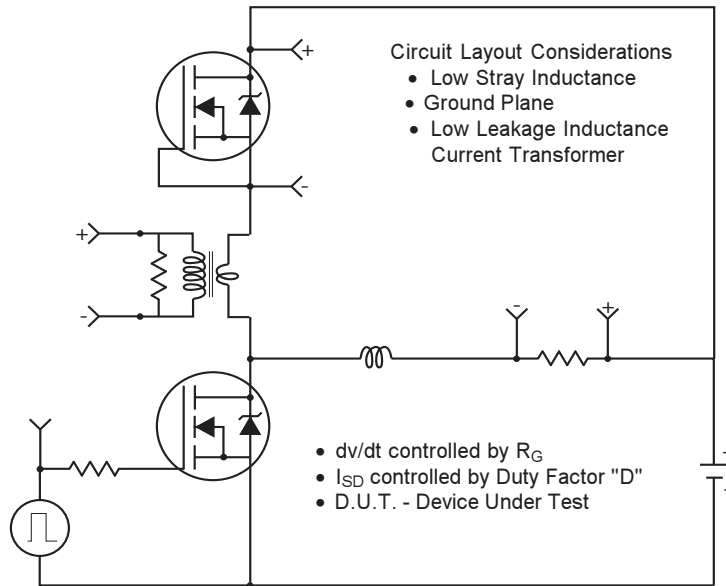
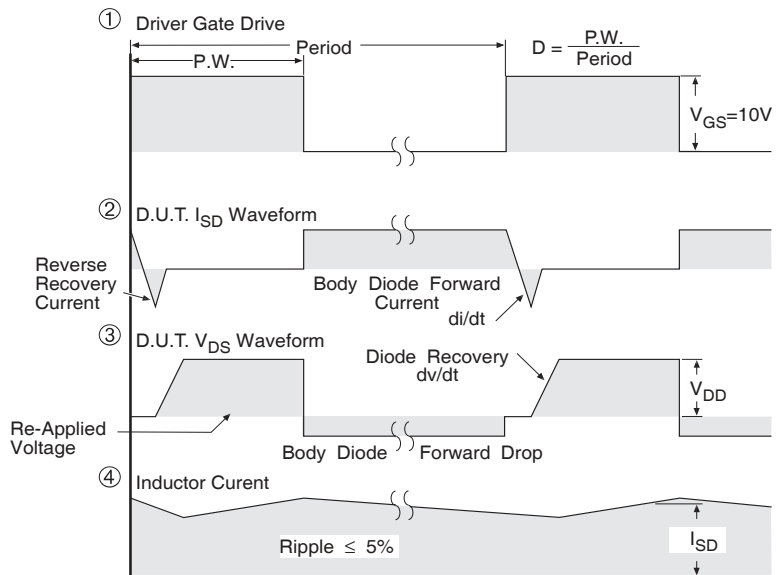


Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



* Reverse Polarity for P-Channel
** Use P-Channel Driver for P-Channel Measurements



*** $V_{GS} = 5.0V$ for Logic Level and $3V$ Drive Devices

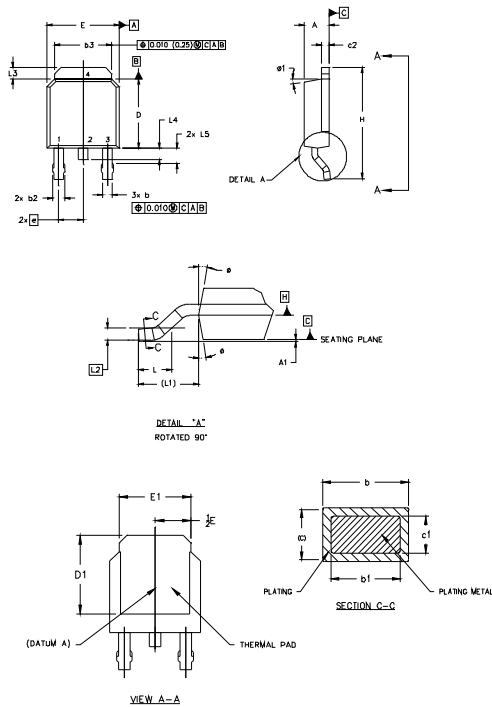
Fig 14 For P Channel HEXFETS

IRFR/U5505PbF

International
IR Rectifier

D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

- 1.0 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
- 2.0 DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS]
- 3.0 LEAD DIMENSION UNCONTROLLED IN L5
- 4.0 DIMENSION D1 AND E1 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
- 5.0 SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 [0.127] AND .010 [0.254] FROM THE LEAD TIP.
- 6.0 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 7.0 OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1		0.11		.005	
b	0.64	0.89	.025	.035	5
b1	0.64	0.79	.025	0.031	5
b2	0.76	1.14	.030	.045	
b3	4.95	5.46	.195	.215	
c	0.46	0.61	.018	.024	5
c1	0.41	0.56	.016	.022	5
c2	.046	0.89	.018	.035	5
D	5.97	6.22	.235	.245	6
D1	5.21	-	.205	-	4
E	6.35	6.73	.250	.265	6
E1	4.32	-	.170	-	4
e	2.29		.090 BSC		
H	9.40	10.41	.370	.410	
L	1.40	1.78	.055	.070	
L1	2.74 REF.		.108 REF.		
L2	0.051 BSC		.020 BSC		
L3	0.89	1.27	.035	.050	
L4		1.02		.040	
L5	1.14	1.52	.045	.060	3
a	0"	10"	0"	10"	
a1	0"	15"	0"	15"	

LEAD ASSIGNMENTS

HEXEET

1.- GATE
2.- DRAIN
3.- SOURCE
4.- DRAIN

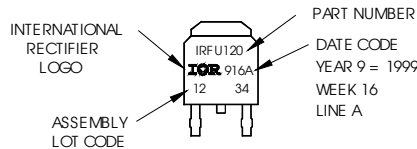
IGBTs, CoPACK

1.- GATE
2.- COLLECTOR
3.- EMITTER
4.- COLLECTOR

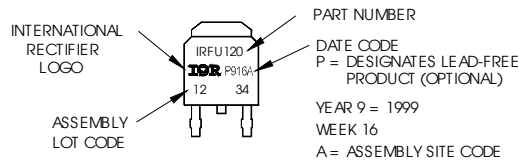
D-Pak (TO-252AA) Part Marking Information

EXAMPLE: THIS IS AN IRFR120
WITH ASSEMBLY
LOT CODE 1234
ASSEMBLED ON VV 16, 1999
IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position
indicates "Lead-Free"



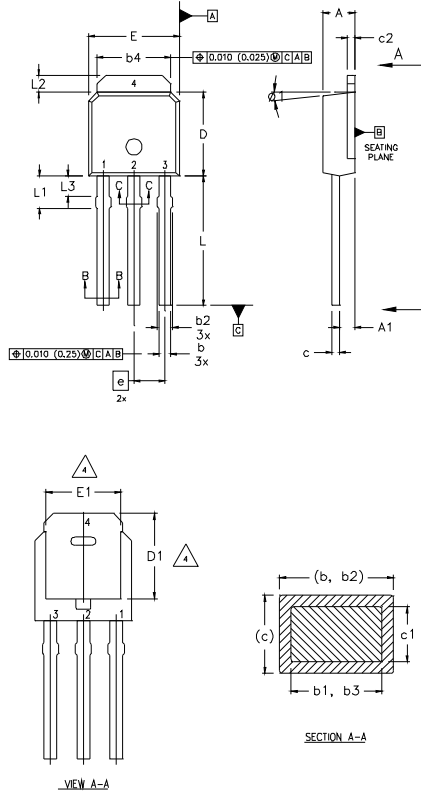
OR



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

I-Pak (TO-251AA) Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

- 1 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
- 2 DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
- 3 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
- 4 THERMAL PAD CONTOUR OPTION WITHIN DIMENSION b4, L2, E1 & D1.
- 5 LEAD DIMENSION UNCONTROLLED IN L3.
- 6 DIMENSION b1, b3 APPLY TO BASE METAL ONLY.
- 7 OUTLINE CONFORMS TO JEDEC OUTLINE TO-251AA.
- 8 CONTROLLING DIMENSION : INCHES.

LEAD ASSIGNMENTS

HEXFET

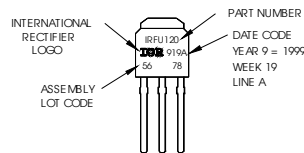
- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	0.086	.094	
A1	0.89	1.14	0.035	0.045	
b	0.64	0.89	0.025	0.035	
b1	0.64	0.79	0.025	0.031	4
b2	0.76	1.14	0.030	0.045	
b3	0.76	1.04	0.030	0.041	
b4	5.00	5.46	0.195	0.215	4
c	0.46	0.61	0.018	0.024	
c1	0.41	0.56	0.016	0.022	
c2	.046	0.86	0.018	0.035	
D	5.97	6.22	0.235	0.245	3, 4
D1	5.21	-	0.205	-	4
E	6.35	6.73	0.250	0.265	3, 4
E1	4.32	-	0.170	-	4
e	2.29		0.090 BSC		
L	8.89	9.60	0.350	0.380	
L1	1.91	2.29	0.075	0.090	
L2	0.89	1.27	0.035	0.050	4
L3	1.14	1.52	0.045	0.060	5
e1	0"	15"	0"	15"	

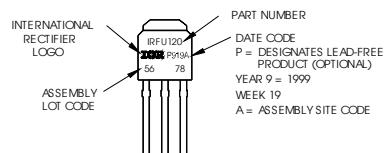
I-Pak (TO-251AA) Part Marking Information

EXAMPLE: THIS IS AN IRFU120
WITH ASSEMBLY
LOT CODE 5678
ASSEMBLED ON WW 19, 1999
IN THE ASSEMBLY LINE "A"

Note: "P" in ass embly line
position indicates "LeadFree"



OR



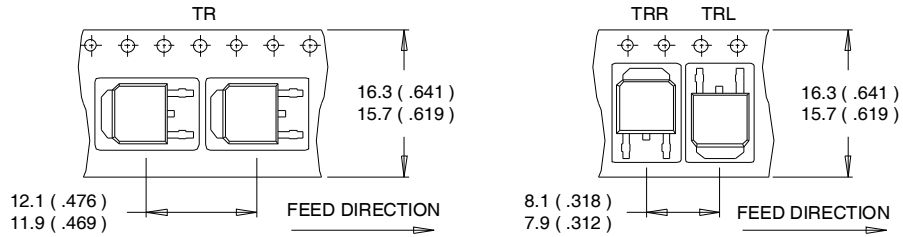
Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

IRFR/U5505PbF

International
IR Rectifier

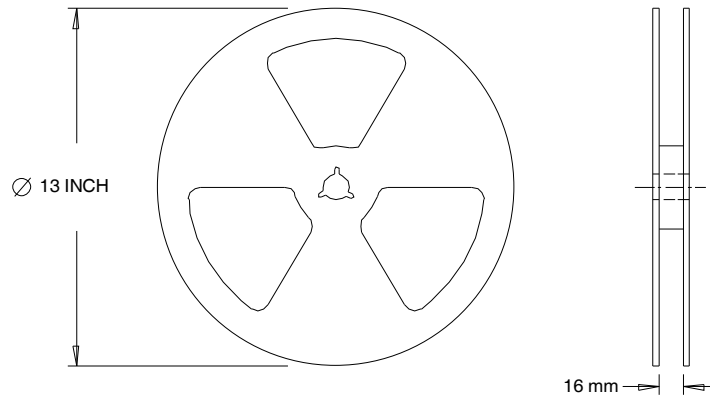
D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :

1. OUTLINE CONFORMS TO EIA-481.

Revision History

Date	Comments
11/6/2012	Added Halogen -Free bullet-pg1

Data and specifications subject to change without notice.

International
IR Rectifier

IR WORLD HEADQUARTERS: 101N.Sepulveda blvd, El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903

Visit us at www.irf.com for sales contact information